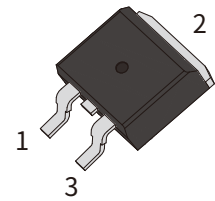


FEATURES

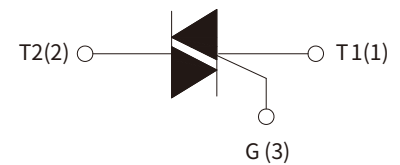
- | Direct interfacing to logic level ICs
- | Direct interfacing to low power gate drive circuits
- | High blocking voltage capability
- | Planar passivated for voltage ruggedness and reliability
- | Triggering in all four quadrant



TO-263

APPLICATIONS

- | General purpose motor control circuits
- | Phase control operations in light dimmers and motor speed controllers
- | Home appliances



Schematic Symbol

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	800	V
RMS on-state current ($T_c=85^\circ\text{C}$)		$I_{\text{T(RMS)}}$	8	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)		I_{TSM}	65	
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	21	A^2S
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	di/dt	50	$\text{A}/\mu\text{s}$
	IV		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{\text{G(AV)}}$	0.5	W
Peak gate power		P_{GM}	5	W
Operating junction temperature range		T_j	$-40 \sim +125$	$^\circ\text{C}$
Storage junction temperature range		T_{STG}	$-40 \sim +150$	

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value				Unit
			D	E	F	G	
I_{GT}	$V_D=12\text{V}$	I - II - III	≤ 5	≤ 10	≤ 25	≤ 50	mA
		IV	≤ 10	≤ 25	≤ 70	≤ 100	
V_{GT}		ALL	≤ 1.3				V
V_{GD}	$V_D=V_{DRM}, R_L=3.3\text{K}\Omega, T_j=125^{\circ}\text{C}$		≥ 0.2				V
I_H	$I_T=100\text{mA}$		≤ 10	≤ 15	≤ 40	≤ 60	mA
I_L	$I_G=1.2I_{GT}$	I - III	≤ 10	≤ 20	≤ 50	≤ 70	
		II - IV	≤ 20	≤ 30	≤ 70	≤ 100	
dV_D/dt	$V_D=67\%V_{DRM}, T_j=125^{\circ}\text{C}$		≥ 20	≥ 50	≥ 50	≥ 200	V/ μs
V_{TM}	$I_{TM}=10\text{A}, t_p=380\mu\text{s}$		≤ 1.6				V
I_{DRM}	$V_D=V_{DRM}, V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	≤ 5				μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	≤ 1				mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case(AC)	3.1	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	Junction to ambient	45	$^{\circ}\text{C}/\text{W}$

PARAMETER CHARACTERISTIC CURVE

FIG.1 Maximum power dissipation versus RMS on-state current

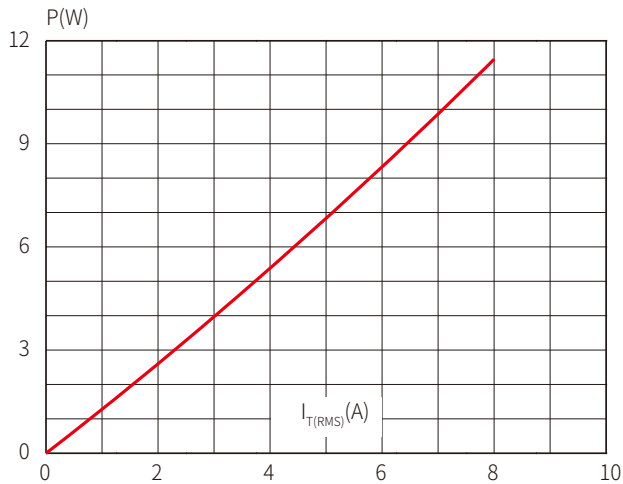


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm)(full cycle)

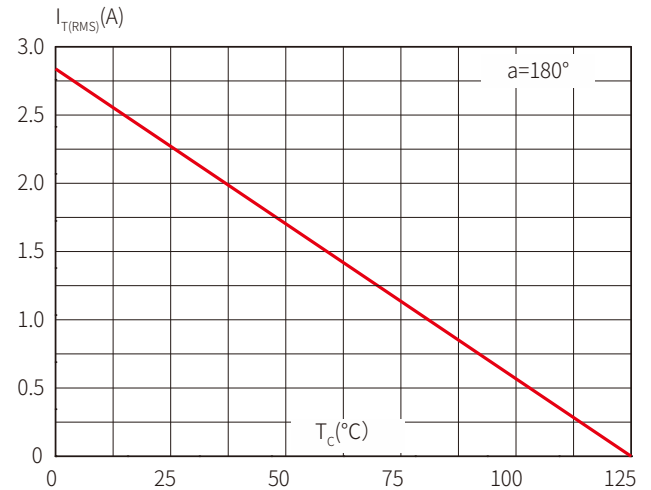


FIG.3: Surge peak on-state current versus number of cycles

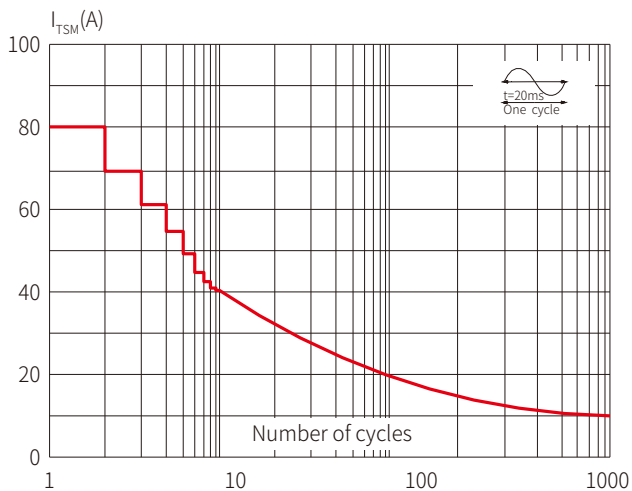


FIG.4 On-state characteristics (maximum values)

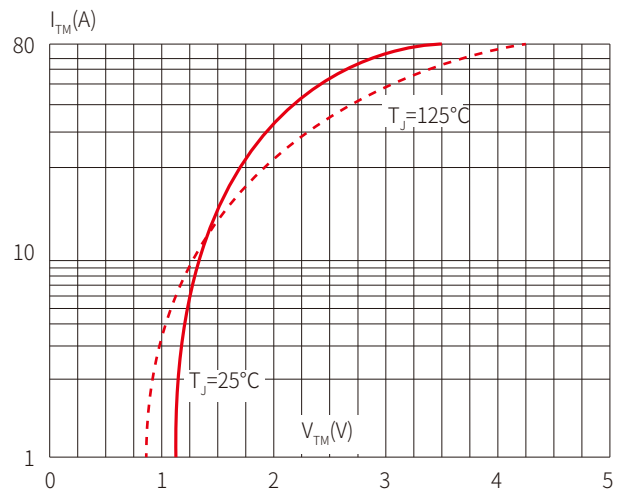


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($dI/dt < 50\text{A}/\mu\text{s}$)

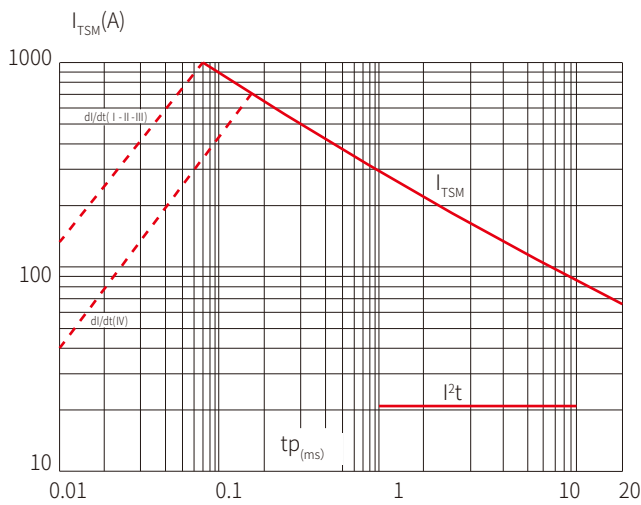


FIG.6 Relative variations of gate trigger current versus junction temperature

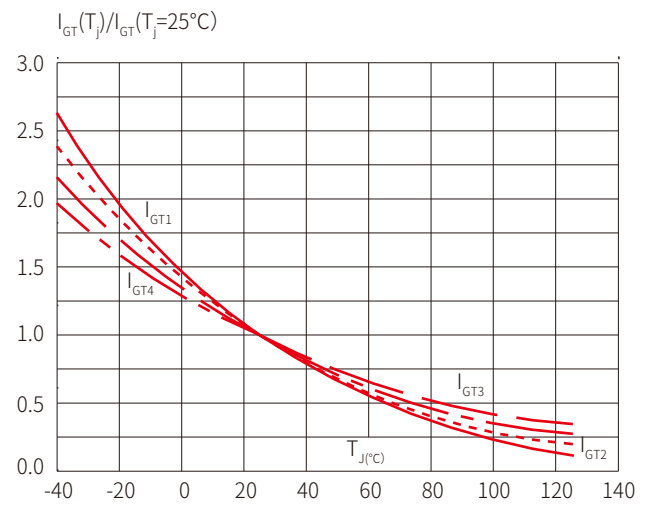


FIG.7 Relative variations of holding current versus junction temperature

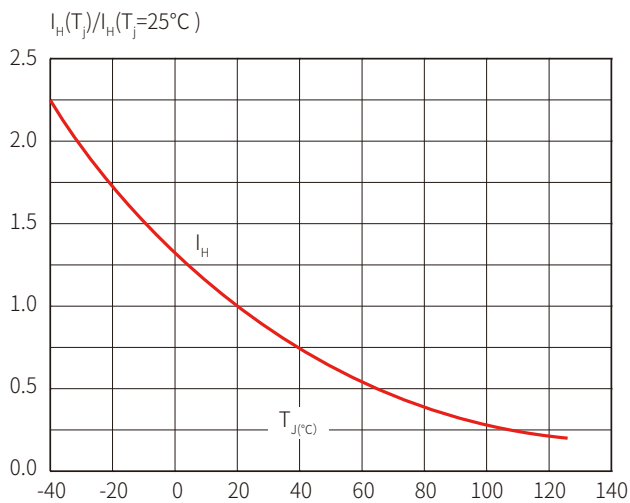
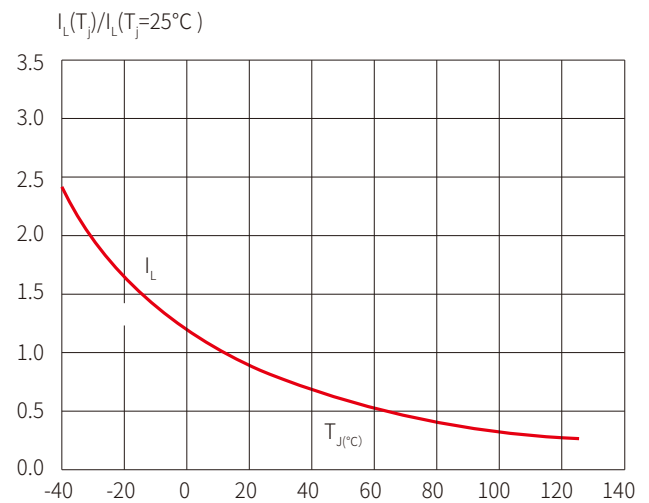
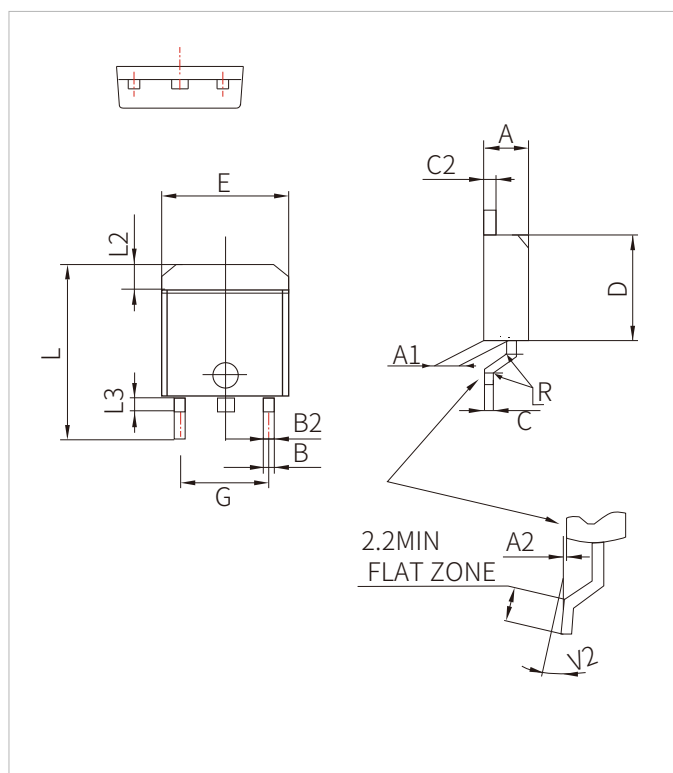


FIG.8 Relative variations of latching current versus junction temperature



TO-263 PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.80	0.169		0.189
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.80		9.50	0.346		0.374
E	9.70		10.40	0.382		0.410
G	4.88		5.28	0.192		0.208
L	14.80		15.85	0.583		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R		0.40			0.016	
V2	0°		8°	0°		8°

ORDERING INFORMATION

Part Number	Package	QTY/Reel	Reel Size
STE8Q80D(E/F/G)	TO-263	800CS	13"

Headquarters

No.3387 Shendu Road
Pujiang I&E Park
Minhang Shanghai China
201000

Hotline

400-021-5756

Web

<https://www.semiware.com>

Sales Center

Tel: 86-21-3463-7458
Email: sales18@semiware.com

Customer Service

Tel: 86-21-5484-1001
Email: sales17@semiware.com

Technical Support

Tel: 86-21-3463-7654
Email: fae01@semiware.com

Complaint & Suggestions

Tel: 86-21-3463-7172
Ext: 8868
Email: cs03@semiware.com

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